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STPS30L30C

Low drop power Schottky rectifier

Features

- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop
- Low thermal resistance
- Avalanche capability specified

Description

This dual center tap Schottky rectifier is suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in TO-220AB, D²PAK and I²PAK, this device is intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.

I _{F(AV)}	2 x 15 A
V _{RRM}	30 V
T _j (max)	150 °C
V _F (typ)	0.37 V

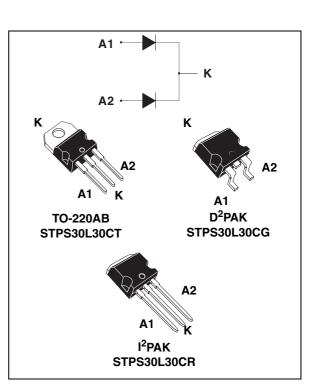
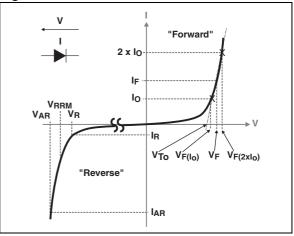


Figure 1. Electrical characteristics ^(a)



a. V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 12* V_{AR} and I_{AR} are pulse measurements ($t_p < 1 \ \mu$ s). V_R , I_R , V_{RRM} and V_F , are static characteristics

1 Characteristics

Table 2.	Absolute ratings	(limiting	values	per diode)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			30	V
I _{F(RMS)}	Forward rms current			30	Α
I _{F(AV)}	Average forward current $\delta = 0.5$	$T_c = 140 \ ^{\circ}C,$ Per diode Per device		15 30	А
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoida	I,	220	Α
I _{RRM}	Peak repetitive reverse current	t _p = 2 μs square, F= 1 kHz square		1	Α
I _{RSM}	Non repetitive peak reverse current	t _p = 100 μs square		3	Α
P _{ARM} ⁽¹⁾	Repetitive peak avalanche power	$t_p = 1 \ \mu s$ $T_j = 25 \ ^\circ C$		5300	W
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage	t _p < 1 μs T _j < 150 °C I _{AR} < 35 A		45	V
V _{ASM} ⁽²⁾	Maximum single pulse peak avalanche voltage			45	V
T _{stg}	Storage temperature range	-65 to + 175	°C		
Tj	Maximum operating junction temperature ⁽³⁾			150	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/µs		

1. For temperature or pulse time duration deratings, refer to *Figure 4*. and *Figure 5*.. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

2. Refer to Figure 12

3. $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3.Thermal resistance⁽¹⁾

Symbol	Parameter	Value	Unit	
R _{th(j-c)}	Junction to case Per diode Total		1.5 0.8	°C/W
R _{th(c)}	Coupling		0.1	

1. When the diodes 1 and 2 are used simultaneously: ΔT_j (diode 1) = P(diode1) x R_{th(j-c)}(Per diode) + P(diode 2) x R_{th(c)})

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _B ⁽¹⁾	Reverse leakage current	T _j = 25 °C	VV			1.5	mA
IR' / Neverse leakage current	T _j = 125 °C	$V_{R} = V_{RRM}$		170	350	mA	
	Forward voltage drop $\begin{array}{c} T_{j} = 25 \ ^{\circ}\text{C} \\ T_{j} = 125 \ ^{\circ}\text{C} \\ \hline T_{j} = 25 \ ^{\circ}\text{C} \\ \hline T_{j} = 25 \ ^{\circ}\text{C} \\ \hline T_{j} = 125 \ ^{\circ}\text{C} \\ \hline T_{j} = 125 \ ^{\circ}\text{C} \\ \hline \end{array}$			0.46			
v (1)		IF = 10 A		0.33	0.37	v	
VF.		$T_j = 25 \ ^{\circ}C$			0.57	v	
		T _j = 125 °C	$I_F = 30A$		0.43	0.5	

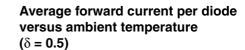
1. Pulse test: $t_p = 380 \ \mu s, \ \delta < 2\%$

To evaluate the conduction losses use the following equation:

 $P = 0.24 \text{ x } I_{F(AV)} + 0.009 \text{ x } I_{F}^{2}(RMS)$



Figure 2. Average forward power dissipation Figure 3. versus average forward current (per diode)



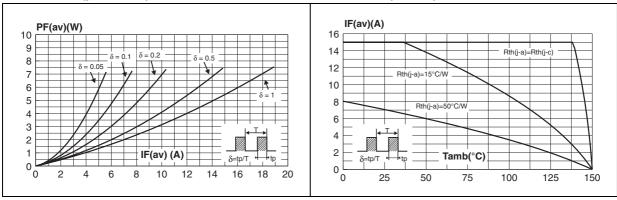


Figure 4. Normalized avalanche power derating versus pulse duration

Figure 5. Normalized avalanche power derating versus junction temperature

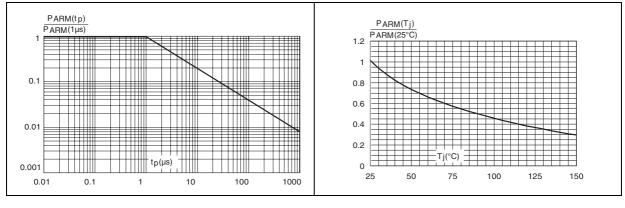


Figure 6. Non repetitive surge peak forward current versus overload duration, (maximum values per diode)

Figure 7. Relative variation of thermal impedance junction to case versus pulse duration

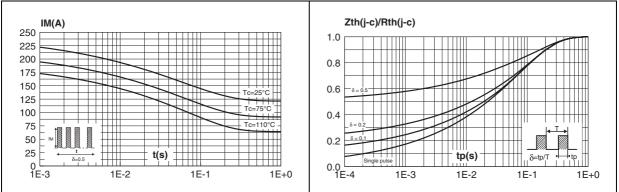


Figure 8. Reverse leakage current versus reverse voltage applied (typical values per diode)

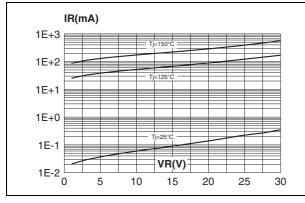
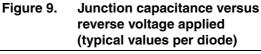


Figure 10. Forward voltage drop versus forward current (maximum values per diode)



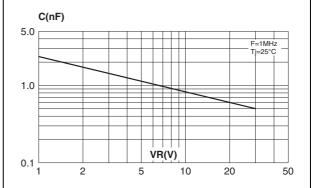


Figure 11. Thermal resistance junction to ambient versus copper surface under tab

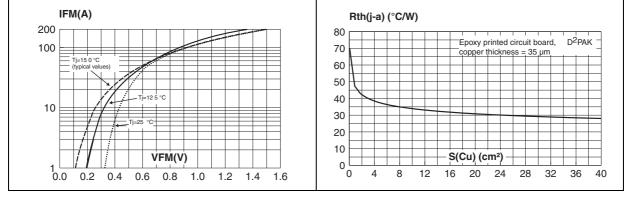
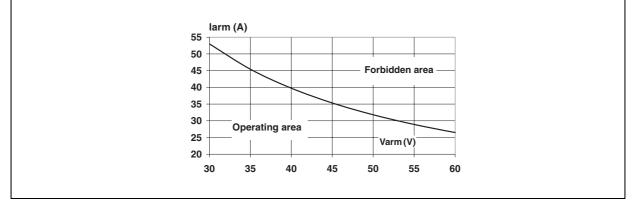


Figure 12. Reverse safe operating area (t_p < 1 μ s and T_j < 150 °C)





2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m

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Table 5. TO-220AB dimensions

			Dimer	nsions	
	Ref.	Millin	neters	Inches	
		Min.	Max.	Min.	Max.
	А	4.40	4.60	0.173	0.181
	С	1.23	1.32	0.048	0.051
H2 A Dia C	D	2.40	2.72	0.094	0.107
	E	0.49	0.70	0.019	0.027
	L7 F	0.61	0.88	0.024	0.034
	F1	1.14	1.70	0.044	0.066
	F2	1.14	1.70	0.044	0.066
F2	G	4.95	5.15	0.194	0.202
	G1	2.40	2.70	0.094	0.106
	H2	10	10.40	0.393	0.409
F→ ←	L2	16.4	typ.	0.64	5 typ.
	L4	13	14	0.511	0.551
	L5	2.65	2.95	0.104	0.116
G G	L6	15.25	15.75	0.600	0.620
	L7	6.20	6.60	0.244	0.259
	L9	3.50	3.93	0.137	0.154
	М	2.6	typ.	0.10	2 typ.
	Diam.	3.75	3.85	0.147	0.151

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Mounting (soldering) the I²PAK metal slug (heatsink) with alloy, like a surface mount device, IS NOT PERMITTED. A standard through-hole mounting is mandatory.

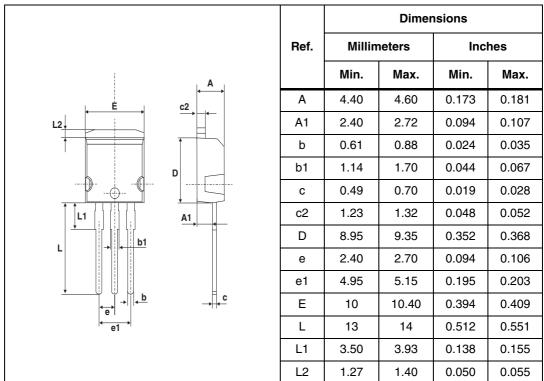


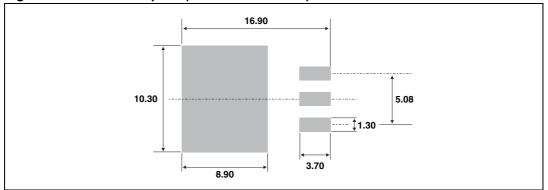
Table 6.I²PAK dimensions



				Dimer	nsions	
		Ref.	Millin	Millimeters		hes
·			Min.	Max.	Min.	Max.
		Α	4.40	4.60	0.173	0.181
		A1	2.49	2.69	0.098	0.106
	C2→→←	A2	0.03	0.23	0.001	0.009
		В	0.70	0.93	0.027	0.037
L		B2	1.14	1.70	0.045	0.067
		С	0.45	0.60	0.017	0.024
↓ ↓ ↓ ↓ ↓ ↓	A1	C2	1.23	1.36	0.048	0.054
		D	8.95	9.35	0.352	0.368
G		E	10.00	10.40	0.393	0.409
		G	4.88	5.28	0.192	0.208
		L	15.00	15.85	0.590	0.624
	M↓ ★↓ V2	L2	1.27	1.40	0.050	0.055
	* FLAT ZONE NO LESS THAN 2mm	L3	1.40	1.75	0.055	0.069
		М	2.40	3.20	0.094	0.126
		R	0.40	typ.	0.016	6 typ.
		V2	0°	8°	0°	8°

Table 7.D²PAK dimensions

Figure 13. D²PAK footprint (dimensions in mm)



3 Ordering information

Table 8.Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS30L30CT	STPS30L30CT	TO-220AB	2.0 g	50	Tube
STPS30L30CG	STPS30L30CR	D ² PAK	1.8 g	50	Tube
STPS30L30CG-TR	STPS30L30CG	D ² PAK	1.8 g	1000	Tape and reel
STPS30L30CG-TR	STPS30L30CG	I ² PAK	1.49 g	50	Tube

4 Revision history

Table 9.Document revision history

Date	Revision	Changes
Jul-2003	5C	Previous issue
29-Apr-2010	6	Added Figure 1 and Figure 12. Added parameters V_{ARM} and V_{ASM} to Table 2



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